



H7P1002DL, H7P1002DS

Silicon P Channel MOS FET
High Speed Power Switching

REJ03G1601-0100

Rev.1.00

Nov 16, 2007

Features

- Low on-resistance
 $R_{DS(on)} = 85 \text{ m}\Omega$ typ.
- Low drive current
- 4.5 V gate drive device can driven from 5 V source

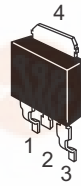
Outline

RENESAS Package code: PRSS0004ZD-B
(Package name: DPAK (L)-(2))

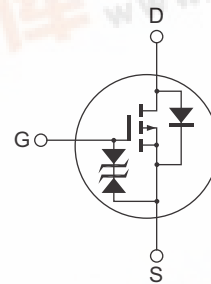


H7P0601DL

RENESAS Package code: PRSS0004ZD-C
(Package name: DPAK (S))



H7P0601DS



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	-100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	-15	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	-60	A
Body-drain diode reverse drain current	I_{DR}	-15	A
Avalanche current	I_{AP} ^{Note3}	-12	A
Avalanche energy	E_{AR} ^{Note3}	14.4	mJ
Channel dissipation	P_{ch} ^{Note2}	30	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$ 2. Value at $T_c = 25^\circ C$ 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$ 

Electrical Characteristics

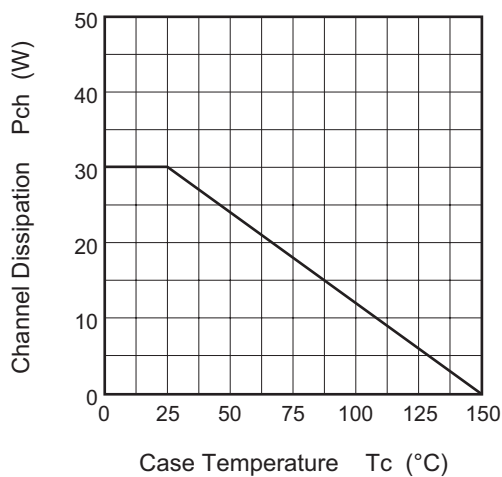
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-100	—	—	V	$I_D = -10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -100 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$I_D = -1 \text{ mA}$, $V_{DS} = -10 \text{ V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	85	105	$\text{m}\Omega$	$I_D = -7.5 \text{ A}$, $V_{GS} = -10 \text{ V}$ ^{Note4}
		—	105	150	$\text{m}\Omega$	$I_D = -7.5 \text{ A}$, $V_{GS} = -4.5 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	7.2	12	—	S	$I_D = -7.5 \text{ A}$, $V_{DS} = -10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	2600	—	pF	$V_{DS} = -10 \text{ V}$
Output capacitance	C_{oss}	—	190	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	120	—	pF	$f = 1 \text{ MHz}$
Total gate charge	Q_g	—	45	—	nC	$V_{DD} = -50 \text{ V}$
Gate to source charge	Q_{gs}	—	6.5	—	nC	$V_{GS} = -10 \text{ V}$
Gate to drain charge	Q_{gd}	—	9.0	—	nC	$I_D = -15 \text{ A}$
Turn-on delay time	$t_{d(on)}$	—	23	—	ns	$V_{GS} = -10 \text{ V}$, $I_D = -7.5 \text{ A}$ $R_L = 4.0 \text{ }\Omega$ $R_g = 4.7 \text{ }\Omega$
Rise time	t_r	—	45	—	ns	
Turn-off delay time	$t_{d(off)}$	—	80	—	ns	
Fall time	t_f	—	13	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-0.91	—	V	$I_F = -15 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	50	—	ns	$I_F = -15 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

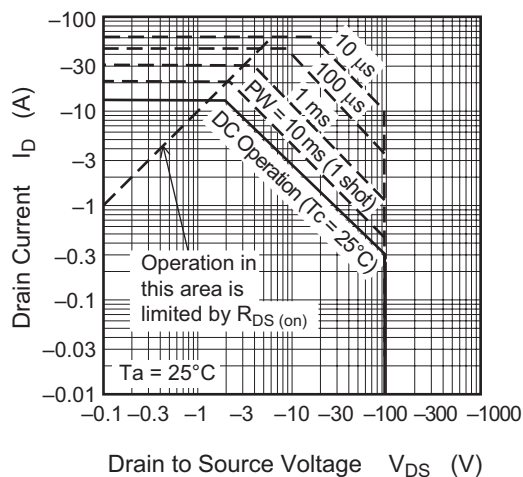
Note: 4. Pulse test

Main Characteristics

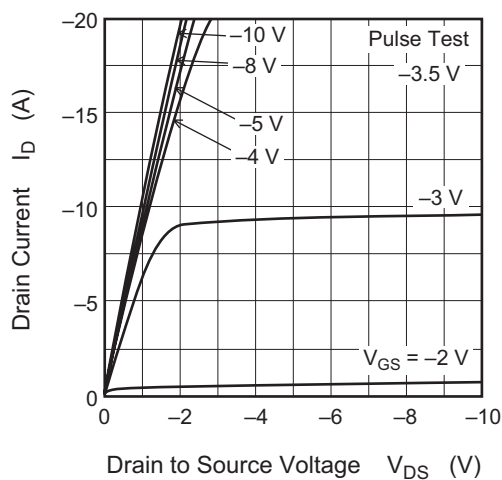
Power vs. Temperature Derating



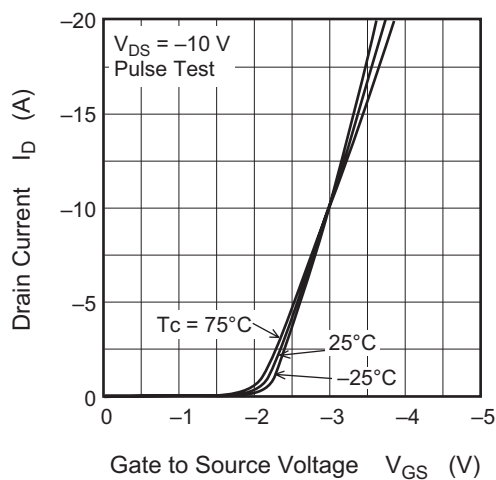
Maximum Safe Operation Area



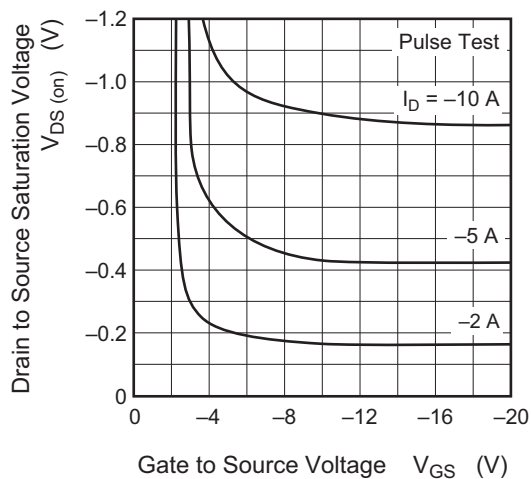
Typical Output Characteristics



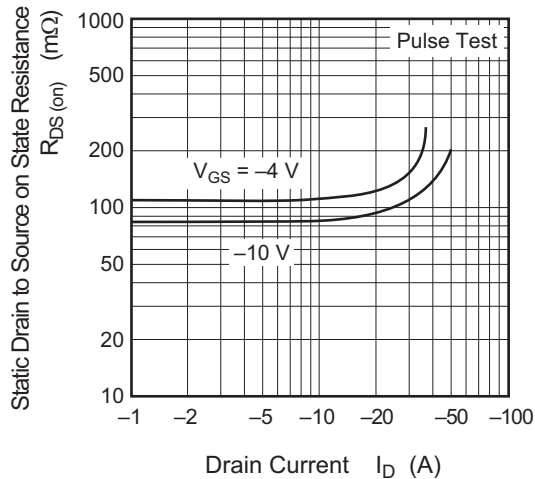
Typical Transfer Characteristics

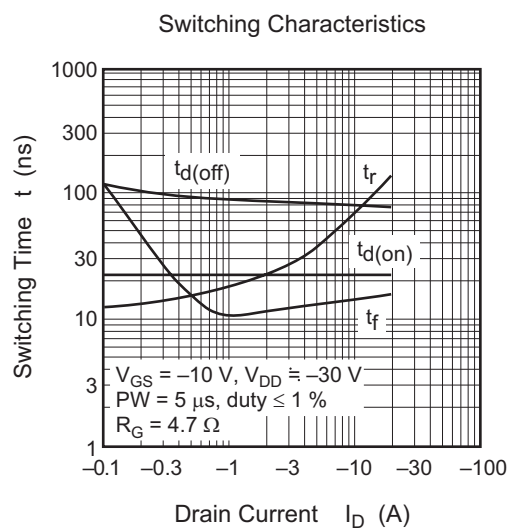
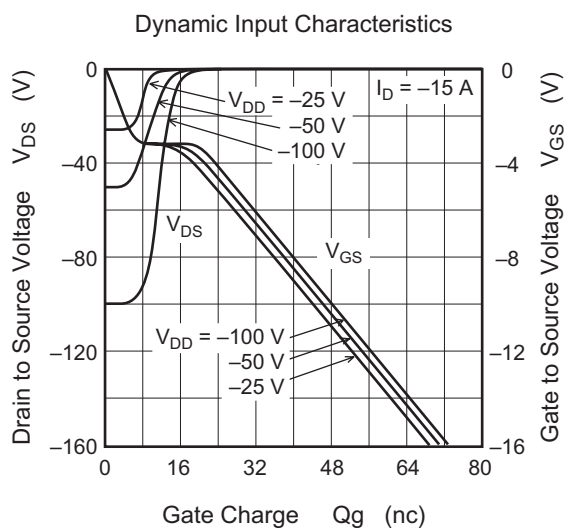
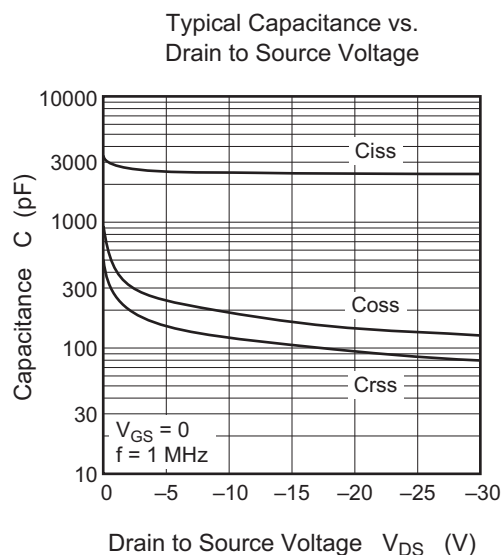
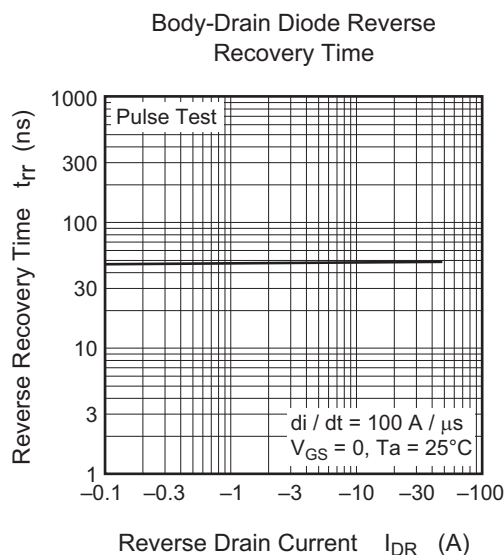
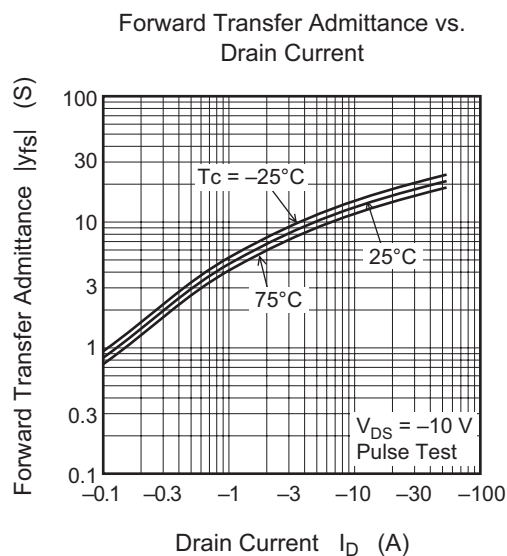
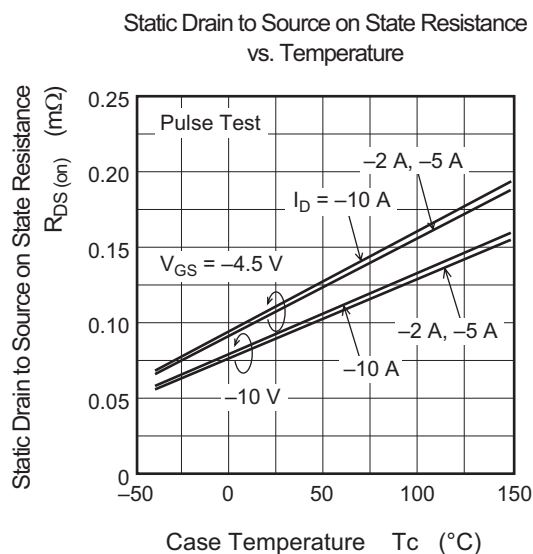


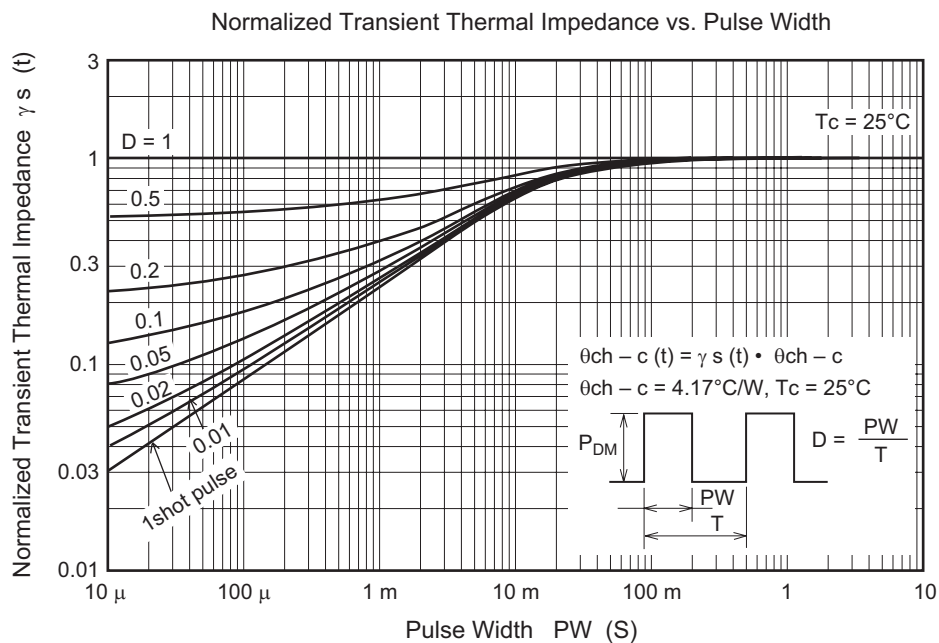
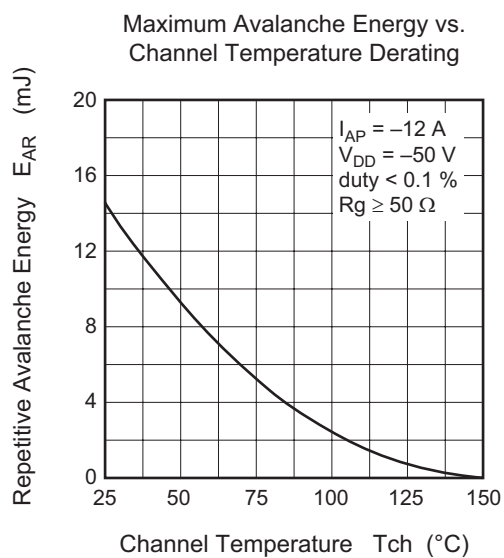
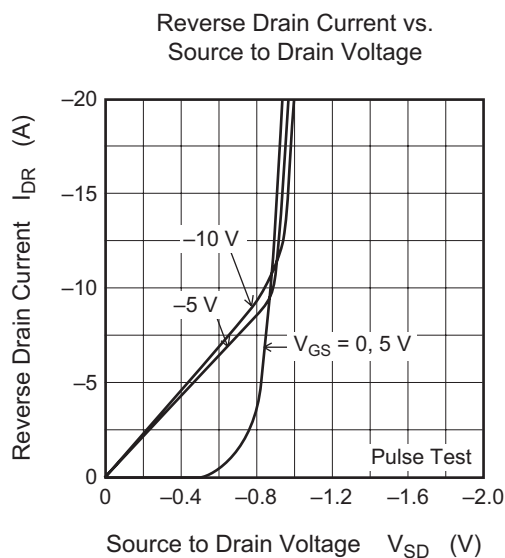
Drain to Source Saturation Voltage vs. Gate to Source Voltage



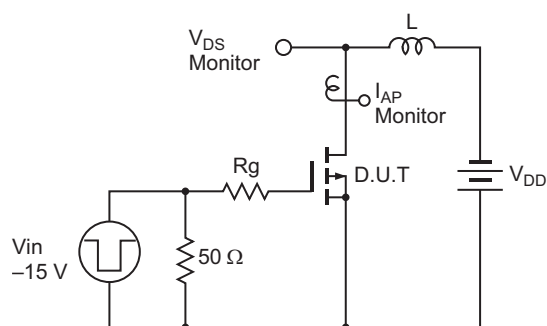
Static Drain to Source on State Resistance vs. Drain Current





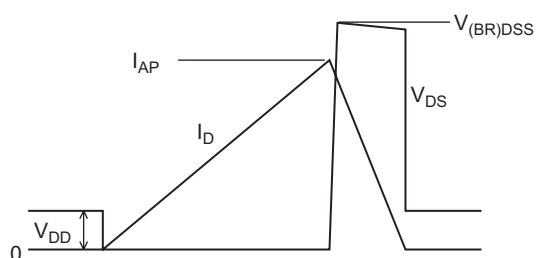


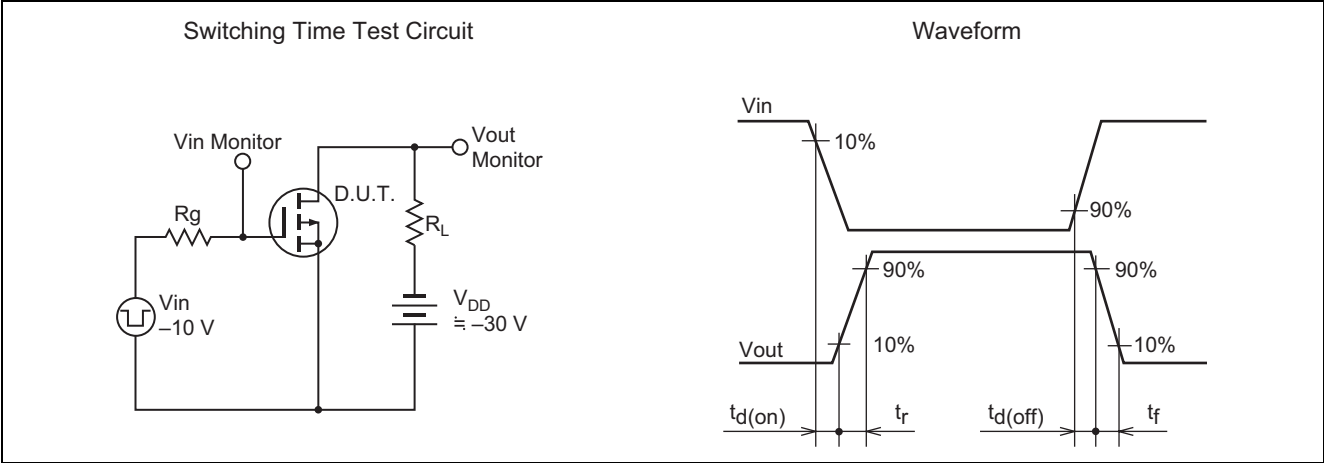
Avalanche Test Circuit



Avalanche Waveform

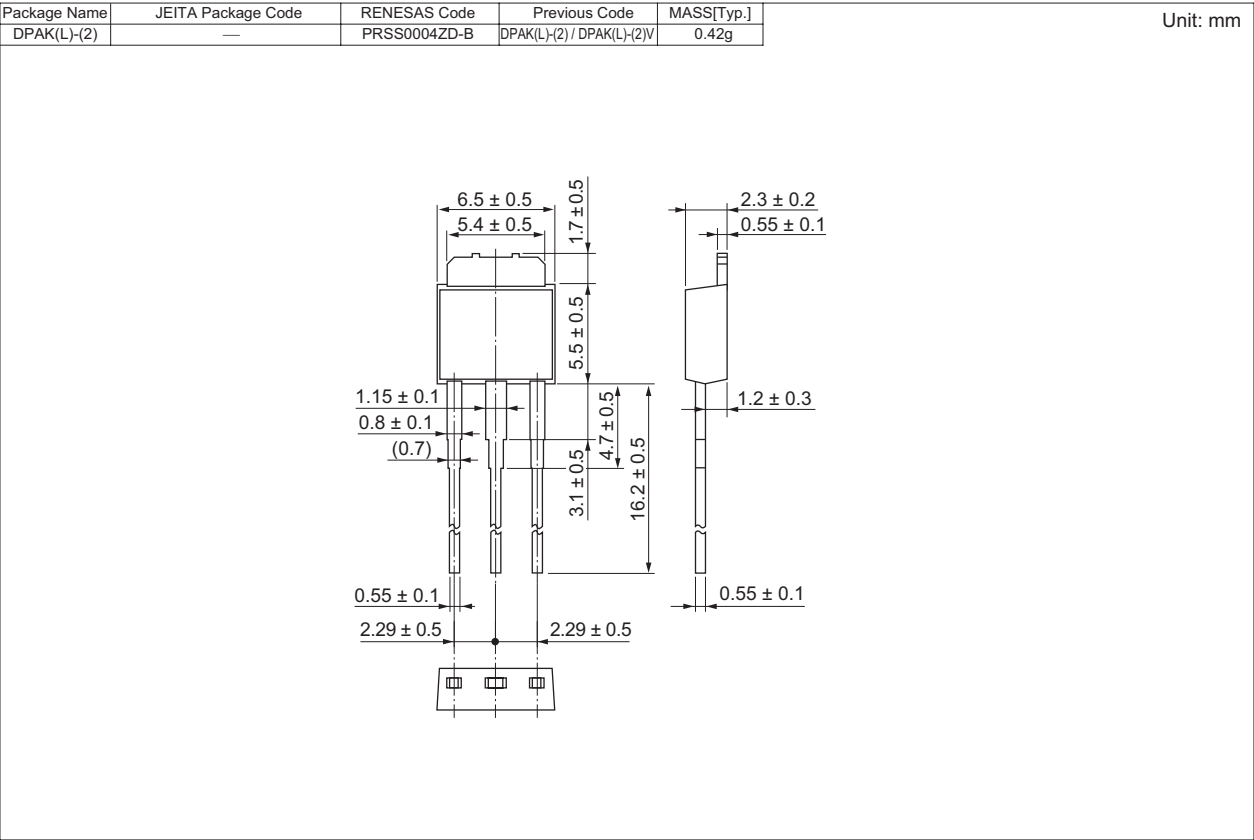
$$E_{AR} = \frac{1}{2} \cdot L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



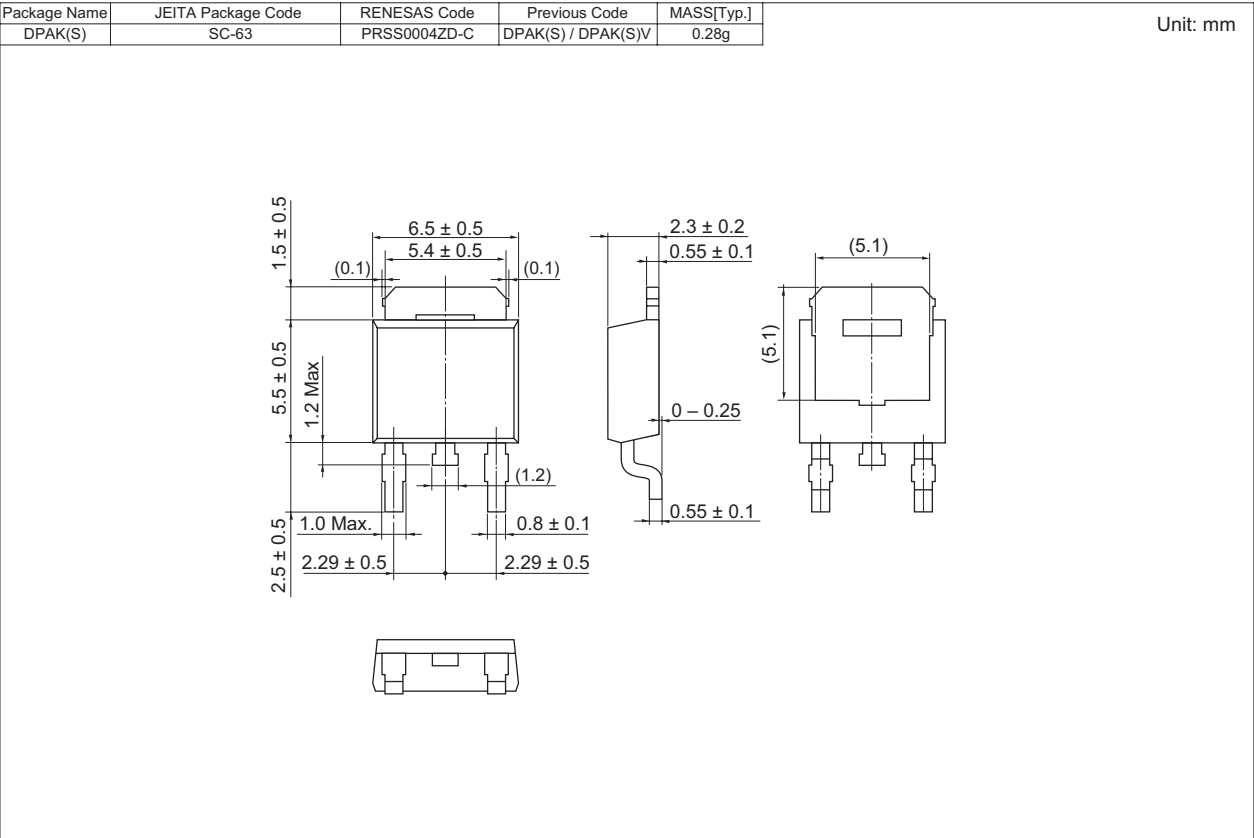


Package Dimensions

• H7P1002DL



• H7P1002DS



Ordering Information

Part No.	Quantity	Shipping Container
H7P1002DL-E	3200 pcs	Hold Box, Radial Taping
H7P1002DSTL-E	3000 pcs	Taping

Notes:

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